

Supporting Information

Nitrogen Doped NiS₂ Nanoarray with Enhanced Electrocatalytic Activity for Water Oxidation

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Experimental Section

Materials:

Ni(NO₃)₂•6H₂O, NH₃•H₂O and sulphur powder were purchased from Sinopharm Chemical Reagent Co. Ltd. (Shanghai, China). The carbon paper (CP) were purchased from Shanghai Hesun Co. Ltd. (Shanghai, China). Other reagents were of analytical grade and were used as received.

Synthesis of Ni(OH)₂ and N doped NiS₂:

The Ni(OH)₂ was synthesized through a simple hydrothermal reaction. Briefly, 60 mg Ni(NO₃)₂•6H₂O was dissolved in 10 mL water to form a homogeneous solution. A piece of CP (1 cm×4 cm) was immersed into above solution and then 0.6 mL NH₃•H₂O was added. The mixture was transferred to a Teflon-lined autoclave and kept at 140 °C for 12 h. After being washed with deionized water and ethanol several times, the product was dried at room temperature. This obtained Ni(OH)₂ product was designated as N₁-Ni(OH)₂. When the amount of ammonium hydroxide were 1.2 and 2.4 mL, the obtained Ni(OH)₂ products were donated as N₂-Ni(OH)₂ and N₃-Ni(OH)₂.

The pure Ni(OH)_2 (donated as $\text{N}_0\text{-Ni(OH)}_2$) was synthesized according to the literature.¹

In a typical synthesis of N doped NiS_2 , the $\text{N}_2\text{-Ni(OH)}_2$ was annealed with sulphur powder. The $\text{N}_2\text{-Ni(OH)}_2$ and sulphur powder (200 mg) were placed separately in a fused silica tube, and sulphur powder was at the upstream side. Then the fused silica tube was heated to 400 °C with a heating rate of 10 °C/min and kept for 1 h under N_2 . The obtained product was donated as $\text{N}_2\text{-NiS}_2\text{-400}$. When the sulfuration temperatures were 500 and 600 °C, the final products were donated as $\text{N}_2\text{-NiS}_2\text{-500}$ and $\text{N}_2\text{-NiS}_2\text{-600}$.

Characterization:

XRD spectra were obtained using a D8 ADVANCE diffractometer (Bruker, Germany) using $\text{Cu K}\alpha$ (1.5406 Å) radiation. SEM images were inspected on a Hitachi S-4800. XPS measurements were performed on an ESCALAB MKII spectrometer (VG Co., United Kingdom) with $\text{Al K}\alpha$ X-ray radiation as the X-ray source for excitation.

Electrochemical Measurements:

All measurements were carried out in a three-electrode electrochemical cell at room temperature with a CHI 614D electrochemical workstation. The obtained N doped $\text{NiS}_2\text{-CP}$ was directly used as the working electrode, while a Pt electrode as the counter electrode and a mercury/mercury oxide electrode (MOE) as the reference electrode. For preparation of the RuO_2 on CP, the RuO_2 was dispersed in ethanol to achieve a concentration of 1 mg mL^{-1} with 4 wt% polytetrafluoroethylene. After sonication for 30 minutes, 250 μL of the RuO_2 ink was drop-dried onto a 1 cm \times 1 cm

CP (loading 0.25 mg cm⁻²). The potential was calibrated with respect to reversible hydrogen electrode potential (RHE), which was determined by a Pt/C electrode as the working electrode in electrolyte saturated with the high purity H₂. Before the electrochemical measurement, the electrolyte (1.0 M KOH) was degassed by bubbling argon for 30 min. EIS spectra were performed at 1.53 V vs. RHE in the frequency range of 10⁻²–10⁶ Hz. The volume of O₂ during a potentiostatic electrolysis experiment was monitored by the water displacement method.²

Turnover frequency (TOF) calculation ³:

$$TOF = \frac{J \times A}{4 \times F \times m} \quad (1)$$

J is the current density. A is the area of the carbon fiber paper electrode. F is the faraday constant (96485 C/mol). m is the number of moles of the active materials that are deposited onto the carbon fiber paper.

DFT calculation:

The electronic properties of N doped NiS₂ were investigated by density functional theory (DFT) calculation using the CASTEP (Cambridge Serial Total Energy Package) package.⁴ The wave functions of the valence electrons were expanded in a plane wave basis set with k-vectors within a specified energy cutoff (300 eV). A 2×3×1 Monkhorst-Pack k-point mesh was employed. The unit cell with a slab along the (001) direction was applied in the calculation. All of the structures were fully optimized and relaxed to the ground state.

The OER process is assumed to involve four elementary reaction steps⁵:





where * and M^* represent an active site and an adsorbed intermediate on the surface, respectively.

The free energy of the adsorbed state of each step was calculated as⁵:

$$\Delta G_a = E(HO^*) - E(*) - E_{H_2O} + 1/2 E_{H_2} + (\Delta ZPE - T\Delta S)_a - eU \quad (2)$$

$$\Delta G_b = E(O^*) - E(HO^*) + 1/2 E_{H_2} + (\Delta ZPE - T\Delta S)_b - eU \quad (3)$$

$$\Delta G_c = E(HOO^*) - E(O^*) - E_{H_2O} + 1/2 E_{H_2} + (\Delta ZPE - T\Delta S)_c - eU \quad (4)$$

$$\Delta G_d = E(*) - E(HOO^*) + E_{O_2} + 1/2 E_{H_2} + (\Delta ZPE - T\Delta S)_d - eU \quad (5)$$

where $E(*)$, $E(HO^*)$, $E(O^*)$, and $E(HOO^*)$ are the energies of the pure surface and the adsorbed surfaces with HO^* , O^* , and HOO^* , respectively. E_{H_2O} and E_{H_2} are the computed energies for the sole H_2O and H_2 molecules, respectively. The total free energy (ΔG) to form one molecule of O_2 was fixed at the value of 4.92 eV. U (vs. RHE) is the electrode potential used for changing all the free-energy steps into downhill.

To evaluate the ΔG on the (001) surface, we sampled five active sites, involving Ni-0, Ni-1, Ni-2, Ni-3, and Ni-4 site (Figure S19).

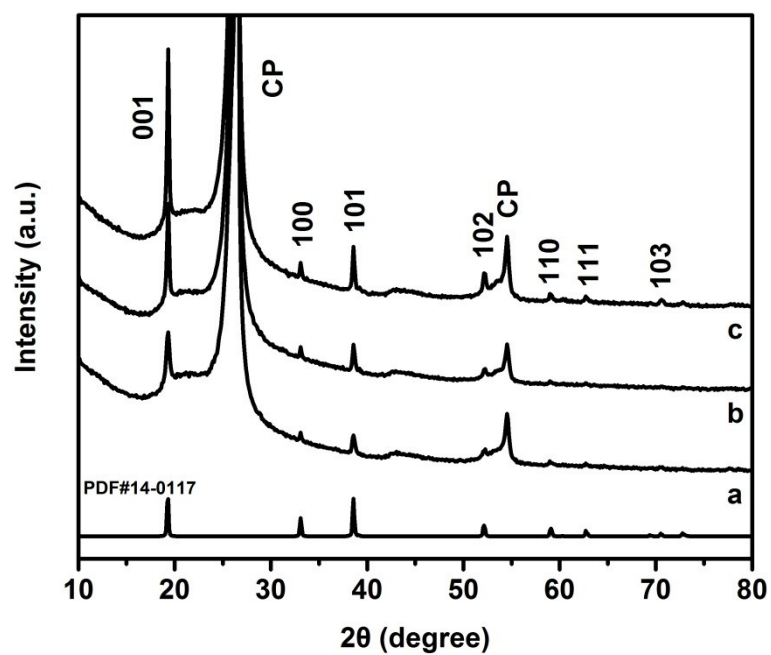


Figure S1. XRD patterns of $\text{N}_1\text{-Ni(OH)}_2$ (a), $\text{N}_2\text{-Ni(OH)}_2$ (b), and $\text{N}_3\text{-Ni(OH)}_2$ (c).

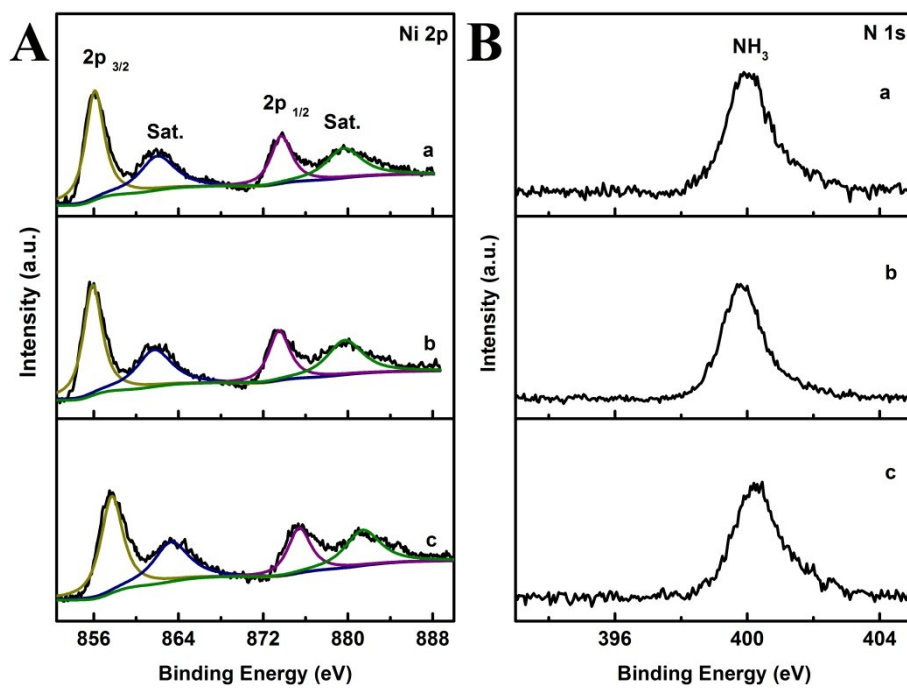


Figure S2. XPS spectra of $\text{N}_1\text{-Ni(OH)}_2$ (a), $\text{N}_2\text{-Ni(OH)}_2$ (b), and $\text{N}_3\text{-Ni(OH)}_2$ (c).

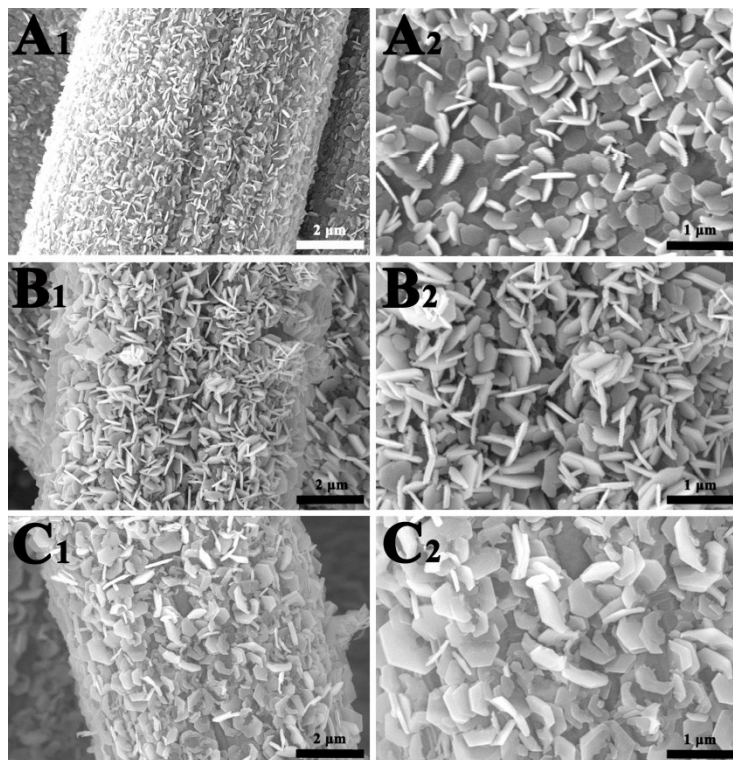


Figure S3. SEM images of N₁-Ni(OH)₂ (A), N₂-Ni(OH)₂ (B), and N₃-Ni(OH)₂ (C).

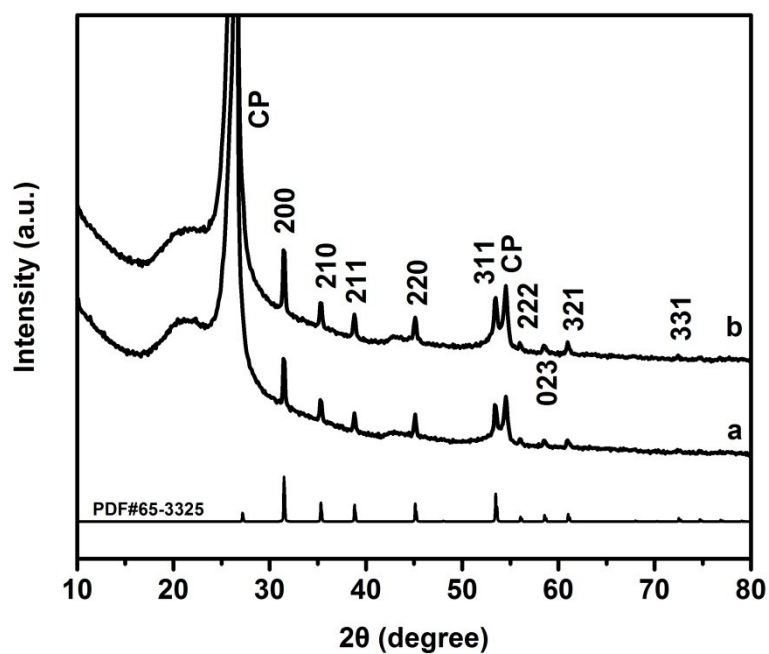


Figure S4. XRD patterns of N₁-NiS₂-500 (a) and N₃-NiS₂-500 (b).

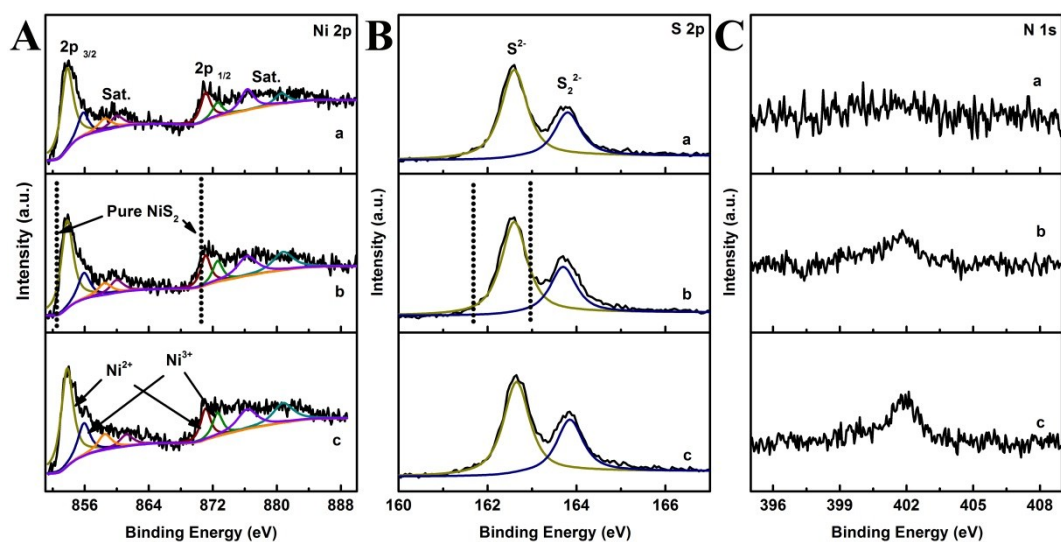


Figure S5. XPS spectra of N_1 -NiS₂-500 (a), N_2 -NiS₂-500 (b), and N_3 -NiS₂-500 (c).

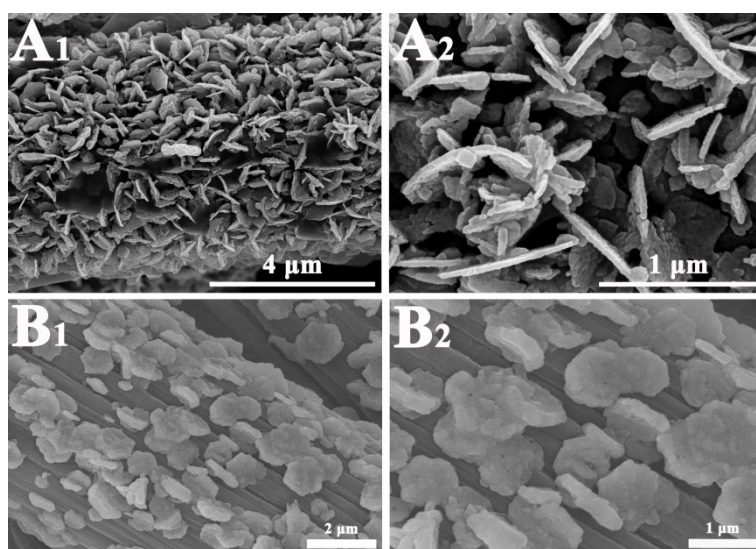


Figure S6. SEM images of N_1 -NiS₂-500 (A) and N_3 -NiS₂-500 (B).

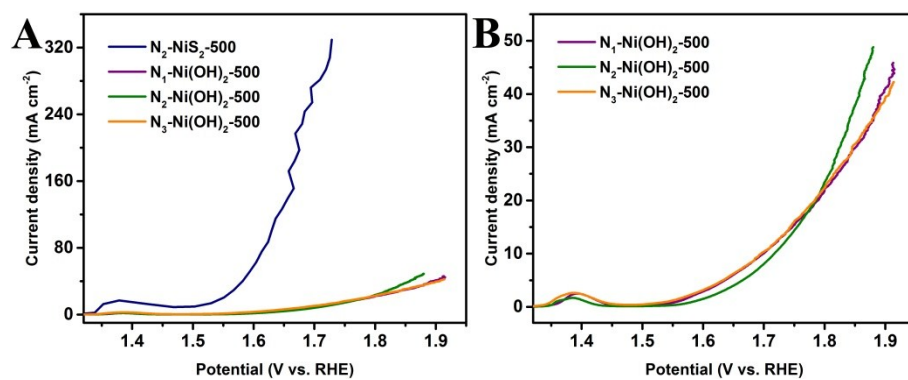


Figure S7. Polarization curves of N_2 -NiS₂-500 and Ni(OH)₂ at higher (A) and (B)

lower current density in 1.0 M KOH at a scan rate of 2 mV s⁻¹.

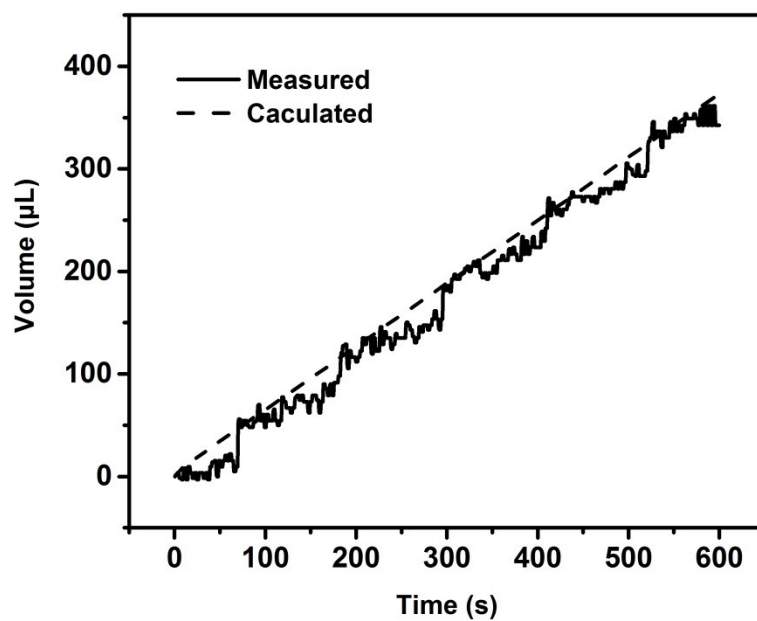


Figure S8. The theoretical and experimental amount of O_2 produced in potentiostatic electrolysis experiments (applied potential: 1.53 V for OER versus RHE).

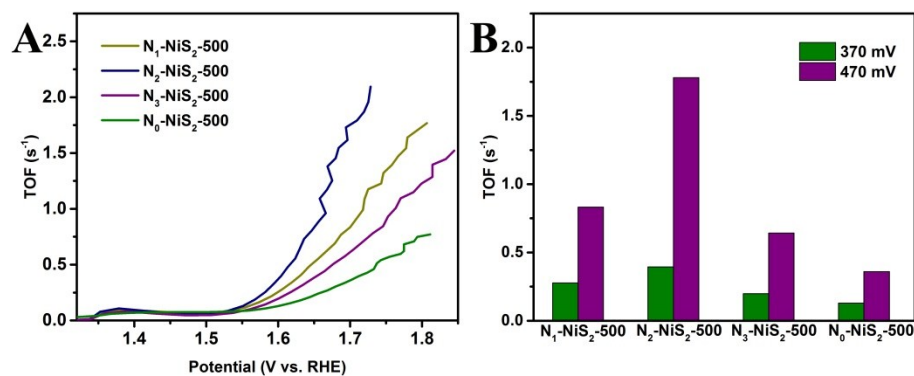


Figure S9. (A) Calculated TOF for N doped NiS_2 . (B) The TOF obtained at different overpotentials.

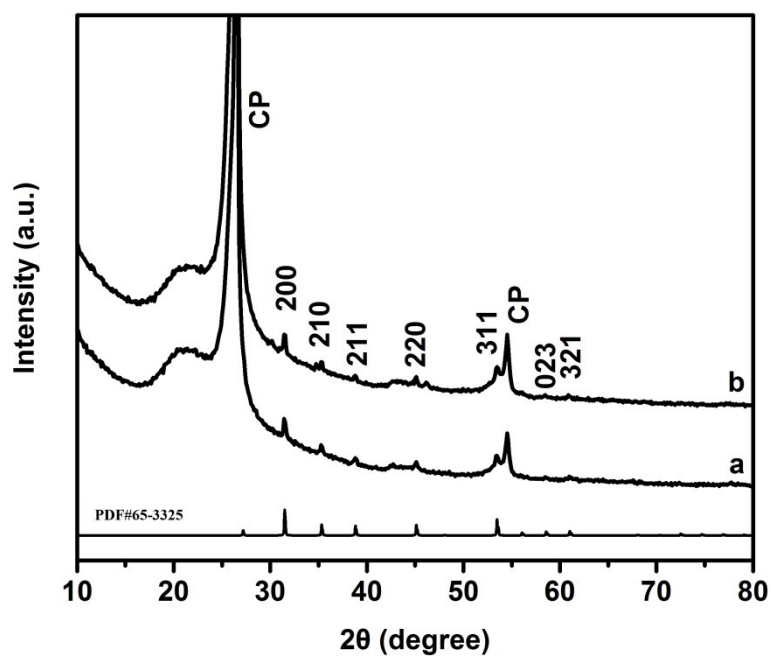


Figure S10. XRD patterns of N_2-NiS_2-400 (a) and N_2-NiS_2-600 (b).

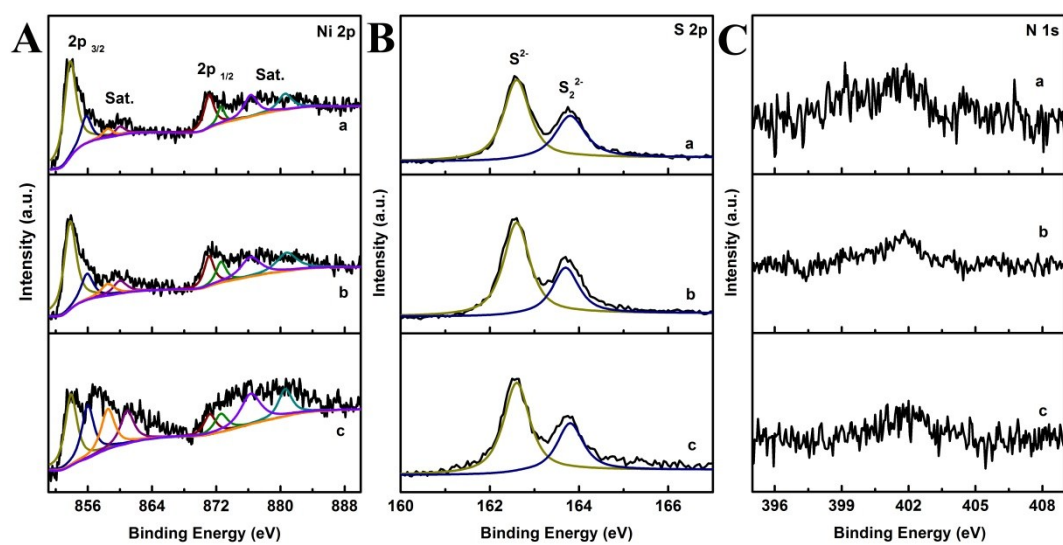


Figure S11. XPS spectra of N_2-NiS_2-400 (a), N_2-NiS_2-500 (b), and N_2-NiS_2-600 (c).

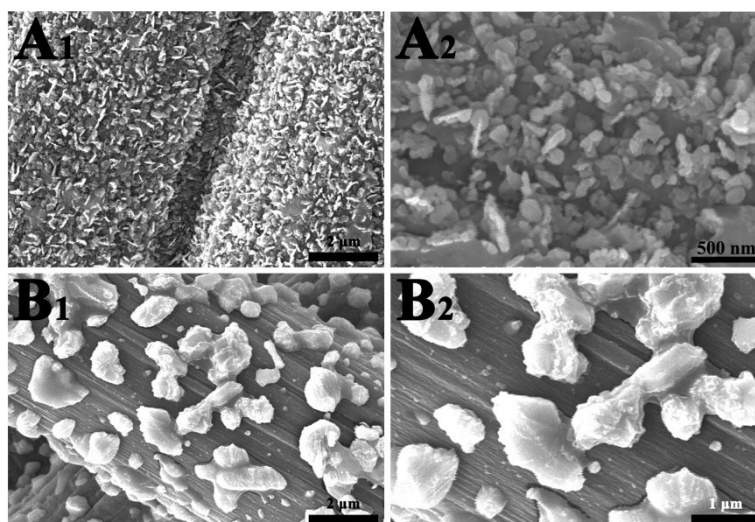


Figure S12. SEM images of N_2 -NiS₂-400 (A) and N_2 -NiS₂-600 (B).

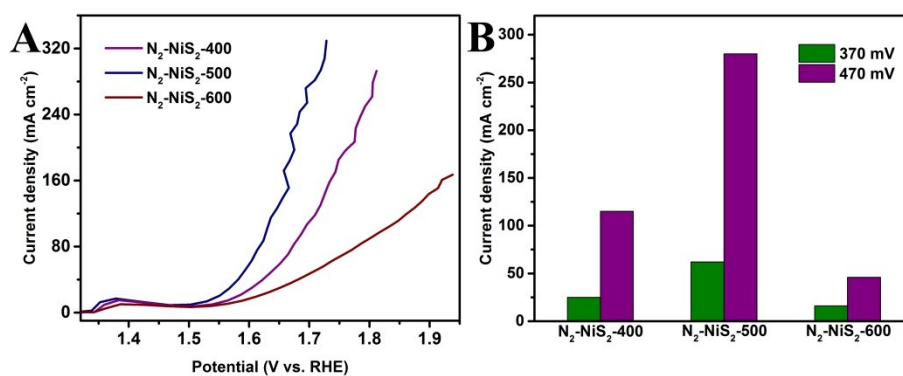


Figure S13. (A) Polarization curves of N doped NiS₂ in 1.0 M KOH at a scan rate of 2 mV s⁻¹ for OER. (B) The current density obtained at different overpotentials.

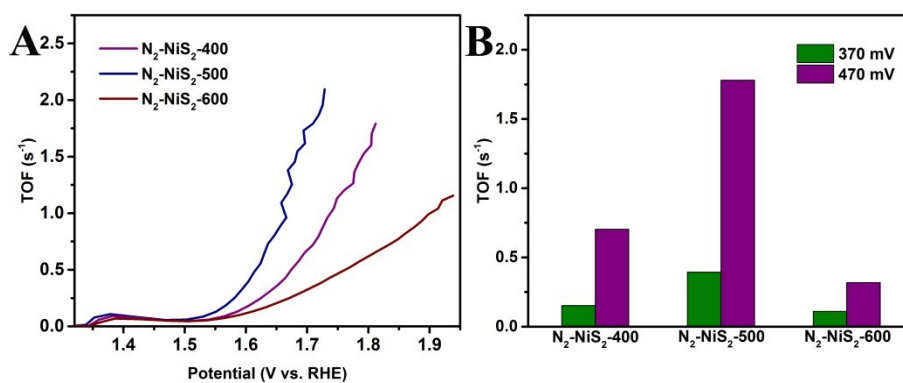


Figure S14. (A) Calculated TOF for N doped NiS₂. (B) The TOF obtained at different overpotentials.

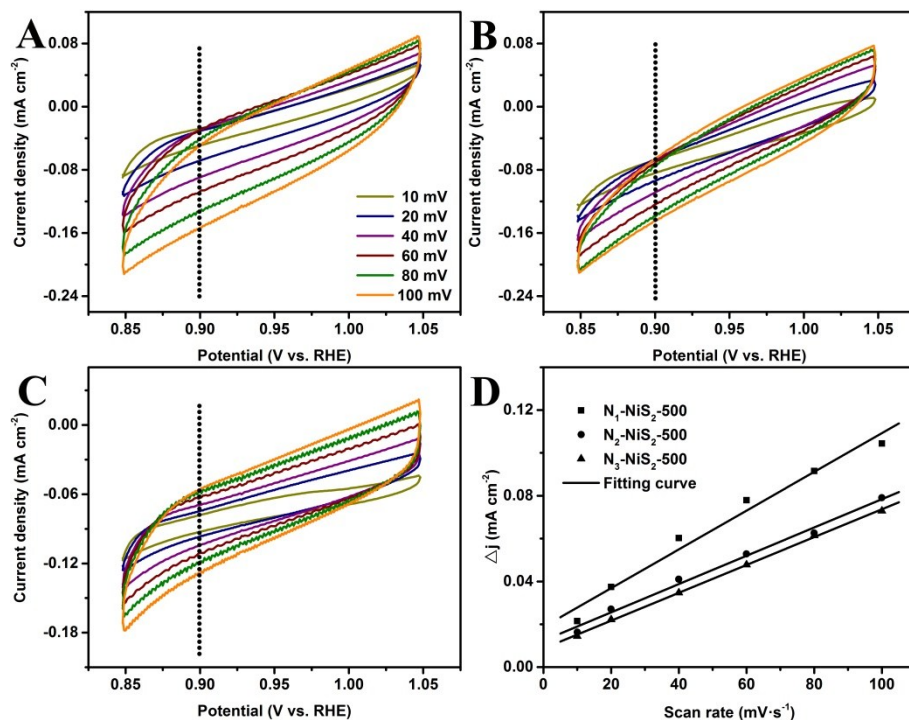


Figure S15. CV curves of N_1 -NiS₂-500 (A), N_2 -NiS₂-500 (B), and N_3 -NiS₂-500 (C) at different scan rates. Current density differences (Δj) plotted against scan rates (D).

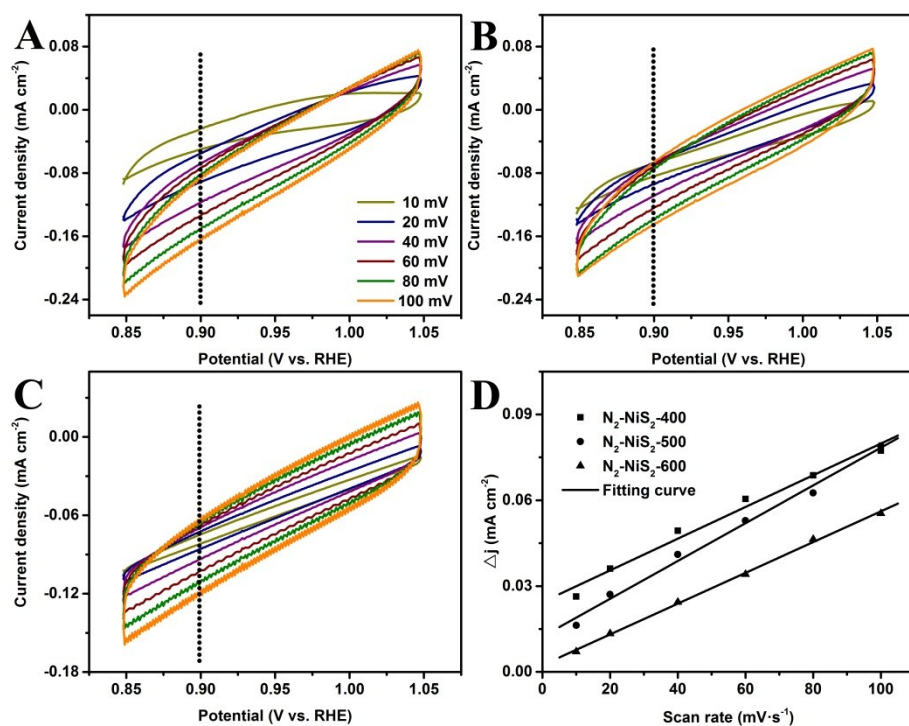


Figure S16. CV curves of N_2 -NiS₂-400 (A), N_2 -NiS₂-500 (B), and N_2 -NiS₂-600 (C) at different scan rates. Current density differences (Δj) plotted against scan rates (D).

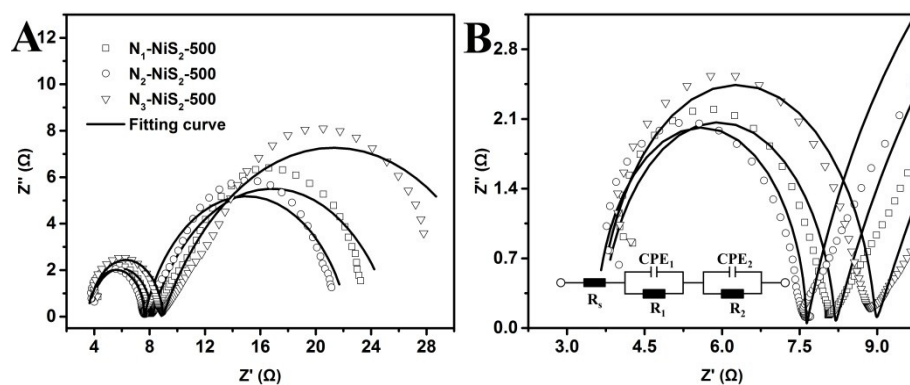


Figure S17. Nyquist plots of EIS spectra measured from N_1 -NiS₂-500, N_2 -NiS₂-500, and N_3 -NiS₂-500.

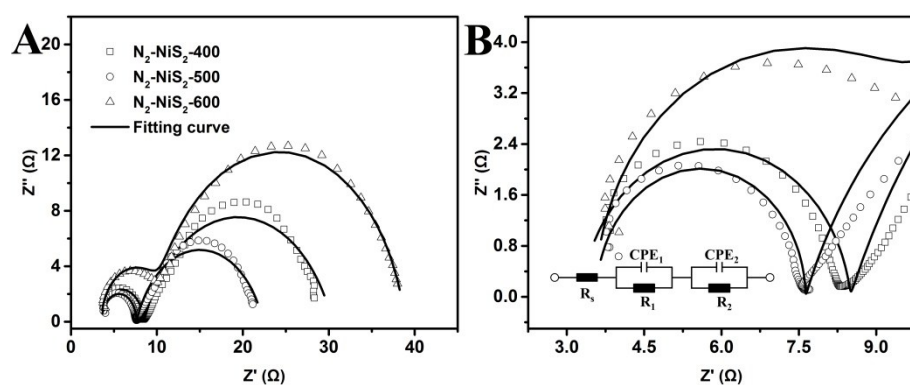


Figure S18. Nyquist plots of EIS spectra measured from N_2 -NiS₂-400, N_2 -NiS₂-500, and N_2 -NiS₂-600.

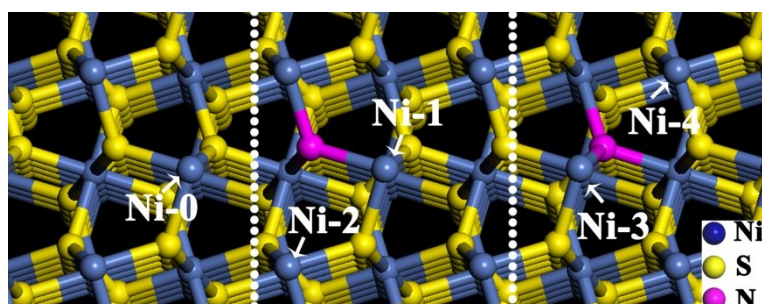


Figure S19. Possible absorption sites on the (001) NiS₂ and N doped NiS₂ surface.

Table S1. Nickel sulfide-based OER electrocatalysts and their performance.

Electrocatalyst	Overpotential (mV)/ mA cm ⁻²	Electrolyte solution	Ref.
N ₂ -NiS ₂ -500	270/ η_{10}	1 M KOH	This work
Ni ₃ S ₂ /Ni foam	310/ η_{10}	0.1M KOH	6
MoS ₂ /Ni ₃ S ₂	218/ η_{10}	1M KOH	7
NiS ₂ /Ti foam	330/ η_{10}	1M KOH	8
High index Ni ₃ S ₂	260/ η_{10}	1M KOH	9
NiS@N/S-C	417/ η_{10}	1M KOH	10
NiS	410/ η_{10}	1M KOH	11
NiS Film	320/ η_{10}	1M KOH	12
NiS/ Ni foam	335/ η_{50}	1M KOH	13
Porous hollow NiS	320/ η_{10}	1M KOH	14
NiS@Stainless steel mesh	297/ η_{10}	0.1M KOH	15
h-NiS _x / Ni foam	180/ η_{10}	1M KOH	16
NiS/ Ni foam	340/ η_{30}	1M KOH	17
NiS Nanowire array	300/ η_{10}	1M KOH	18

Table S2. OER electrocatalysts and their performance.

Electrocatalyst	Overpotential (mV) at η_{10}	Electrolyte solution	Ref.
N ₂ -NiS ₂ -500	270	1 M KOH	This work
FeCoW	191	1M KOH	19
NiFe-LDH/CNTs	247	1M KOH	3
FeCoW/Ni foam	250	1M KOH	20
NiCoP/C	330	1M KOH	21
Co ₄ N	257	1M KOH	22
Porous MoO ₂	260	1M KOH	23
NiFe LDH	260	1M KOH	24
Co-Fe-P	280	1M KOH	25
Co ₃ O ₄ /CNTs	290	0.1M KOH	26
Ni ₃ Se ₂	290	0.3 M KOH	27
NiCo ₂ O ₄	290	1M NaOH	28
CoN	290	1M KOH	29

Table S3. The fitting results of EIS spectra shown in Figure 17A and 18A using the equivalent circuit in their inset.

Sample	R_s (Ω)	CPE_1 ($F \cdot cm^{-2}$)	n_1	R_1 (Ω)	CPE_2 ($F \cdot cm^{-2}$)	n_2	R_2 (Ω)
N ₁ -NiS ₂ -500	3.66	6.44e ⁻⁷	0.94	4.52	0.055	0.72	17.35
N ₂ -NiS ₂ -500	3.57	3.50e ⁻⁷	0.99	4.06	0.055	0.78	14.74
N ₃ -NiS ₂ -500	3.61	5.52e ⁻⁷	0.94	5.36	0.042	0.68	24.69
N ₂ -NiS ₂ -400	3.27	6.45e ⁻⁷	0.92	5.23	0.033	0.77	21.91
N ₂ -NiS ₂ -600	3.55	2.40e ⁻⁷	0.98	6.29	9.64e-6	0.89	29.02

Table S4. The comparison of OER performance with different factors.

Sample	N ₂ -NiS ₂ -500	N ₁ -NiS ₂ -500	N ₂ -NiS ₂ -400	N ₃ -NiS ₂ -500	N ₂ -NiS ₂ -600
OER performance	+++++	++++	+++	++	+
Morphology	++	+++++	++++	+++	+
EASA	++++	+++++	++	+++	+
R_2	+++++	++++	+++	++	+
Ni ³⁺ /Ni ²⁺	+++	++	+++++	++++	+
N content	+++++ (5.4%)	++++ (4.8%)	+++ (3.6%)	++ (3.1%)	+ (2.3%)

Table S5. ΔG of different sites.

Site	Ni-0	Ni-1	Ni-2	Ni-3	Ni-4
ΔG_a (eV)	1.005	0.962	0.994	1.226	1.036
ΔG_b (eV)	2.411	2.007	2.417	0.890	1.974
ΔG_c (eV)	0.934	1.185	0.933	2.222	1.304
ΔG_{*OH} (eV)	1.005	0.961	0.994	1.226	1.036
ΔG_{*O} (eV)	3.416	2.968	3.410	2.116	3.010
ΔG_{*OOH} (eV)	4.350	4.153	4.344	4.338	4.314

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